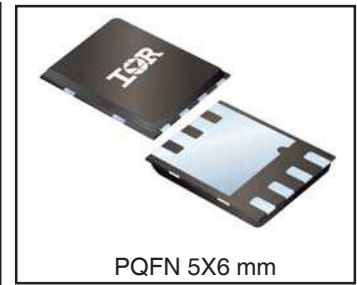
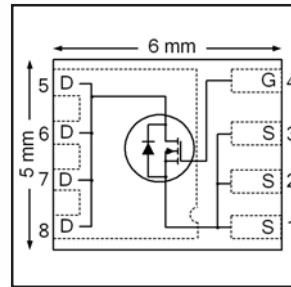


IRFH5020PbF

HEXFET® Power MOSFET

V_{DS}	200	V
$R_{DS(on) \max}$ (@ $V_{GS} = 10V$)	55	mΩ
Q_g (typical)	36	nC
R_G (typical)	1.9	Ω
I_D (@ $T_{c(Bottom)} = 25^\circ C$)	34	A



Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

Features and Benefits

Features

Low $R_{DS(on)}$
Low Thermal Resistance to PCB ($\leq 0.8^\circ C/W$)
100% R_g tested
Low Profile (≤ 0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in
⇒

Benefits

Lower Conduction Losses
Enable better thermal dissipation
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFH5020TRPBF	PQFN 5mm x 6mm	Tape and Reel	4000	
IRFH5020TR2PBF	PQFN 5mm x 6mm	Tape and Reel	400	

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	200	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.1	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.1	
$I_D @ T_{c(Bottom)} = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	34	
$I_D @ T_{c(Bottom)} = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	21	
$I_D @ T_{c(Top)} = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.8	
$I_D @ T_{c(Top)} = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.9	
I_{DM}	Pulsed Drain Current ①	63	W
$P_D @ T_A = 25^\circ C$	Power Dissipation ⑤	3.6	
$P_D @ T_{c(Top)} = 25^\circ C$	Power Dissipation ④	8.3	
	Linear Derating Factor ④	0.07	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Notes ① through ⑤ are on page 8

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

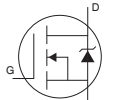
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	47	55	m Ω	$V_{GS} = 10V, I_D = 7.5A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 150\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-12	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	1.0	mA	$V_{DS} = 200V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	18	—	—	S	$V_{DS} = 50V, I_D = 7.5A$
Q_g	Total Gate Charge	—	36	54	nC	$V_{DS} = 100V$ $V_{GS} = 10V$ $I_D = 7.5A$ See Fig.17 & 18
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	8.6	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	2.1	—		
Q_{gd}	Gate-to-Drain Charge	—	11	—		
Q_{godr}	Gate Charge Overdrive	—	14	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	13	—		
Q_{oss}	Output Charge	—	13	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	1.9	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	9.3	—	ns	$V_{DD} = 100V, V_{GS} = 10V$ $I_D = 7.5A$ $R_G = 1.8\Omega$ See Fig.15
t_r	Rise Time	—	7.7	—		
$t_{d(off)}$	Turn-Off Delay Time	—	21	—		
t_f	Fall Time	—	6.0	—		
C_{iss}	Input Capacitance	—	2290	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	120	—		$V_{DS} = 100V$
C_{rss}	Reverse Transfer Capacitance	—	33	—		$f = 1.0MHz$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	320	mJ
I_{AR}	Avalanche Current ①	—	7.5	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	7.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	63		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 7.5A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	46	69	ns	$T_J = 25^\circ\text{C}, I_F = 7.5A, V_{DD} = 100V$
Q_{rr}	Reverse Recovery Charge	—	97	150	nC	$di/dt = 500A/\mu s$ ③
t_{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				



Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case	—	0.8	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	15	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	35	
$R_{\theta JA} (<10s)$	Junction-to-Ambient ⑤	—	33	

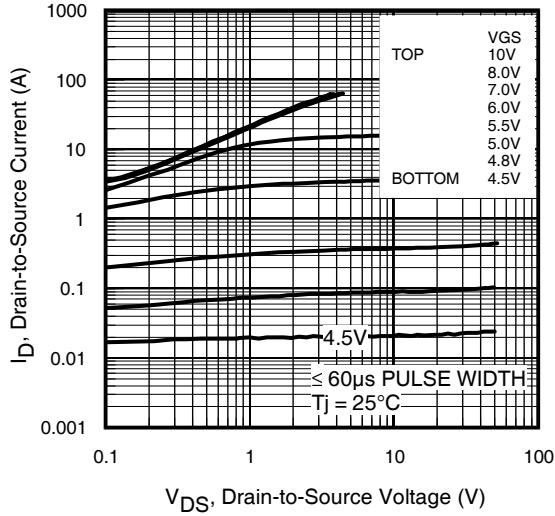


Fig 1. Typical Output Characteristics

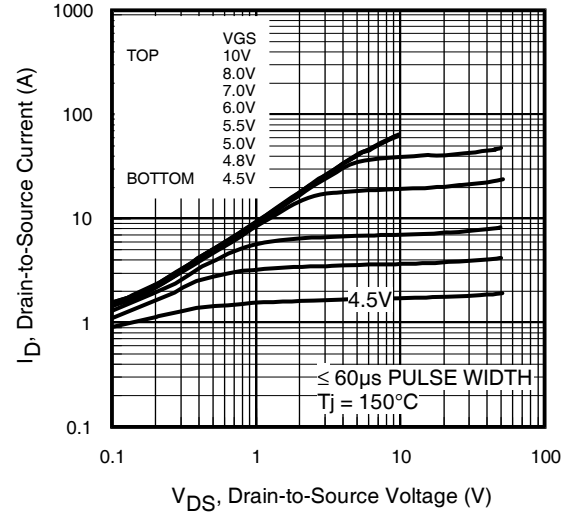


Fig 2. Typical Output Characteristics

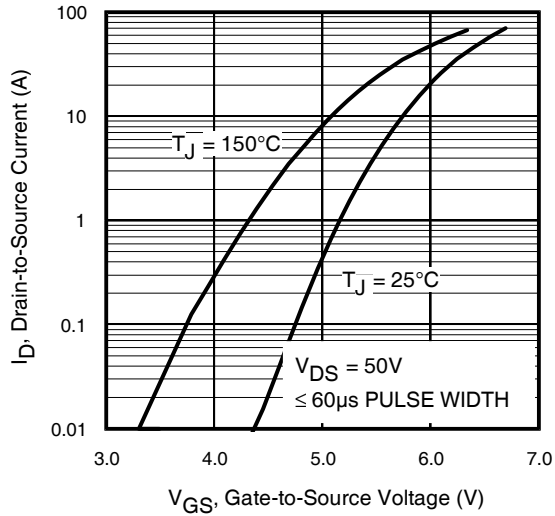


Fig 3. Typical Transfer Characteristics

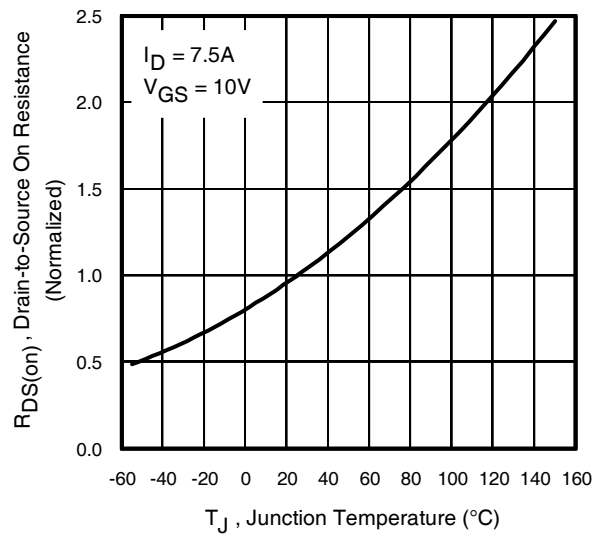


Fig 4. Normalized On-Resistance Vs. Temperature

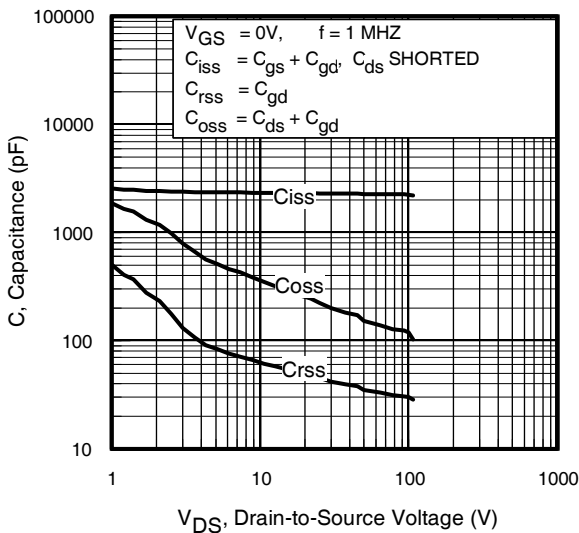


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage
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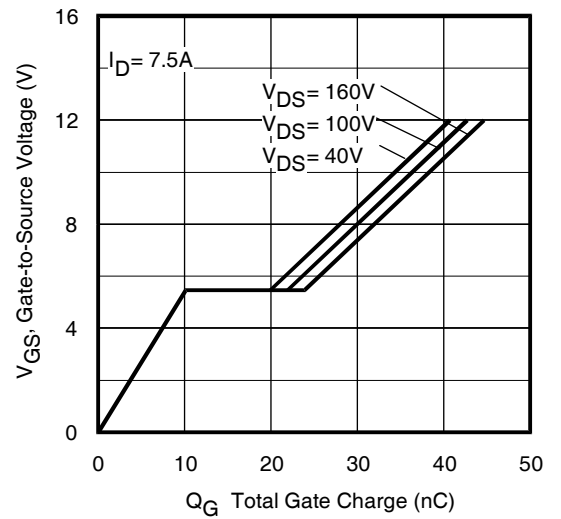


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

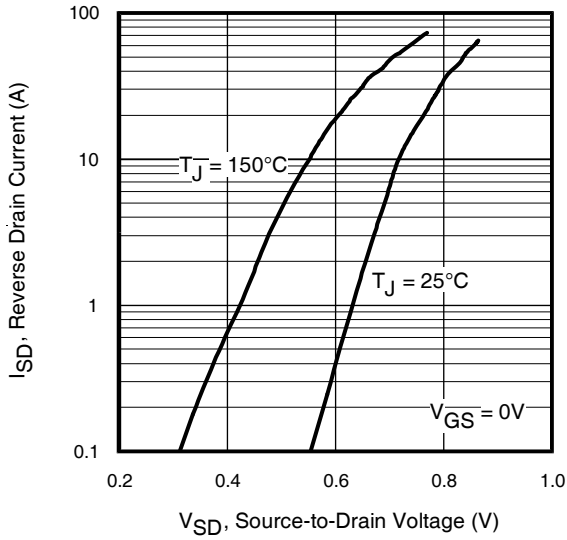


Fig 7. Typical Source-Drain Diode Forward Voltage

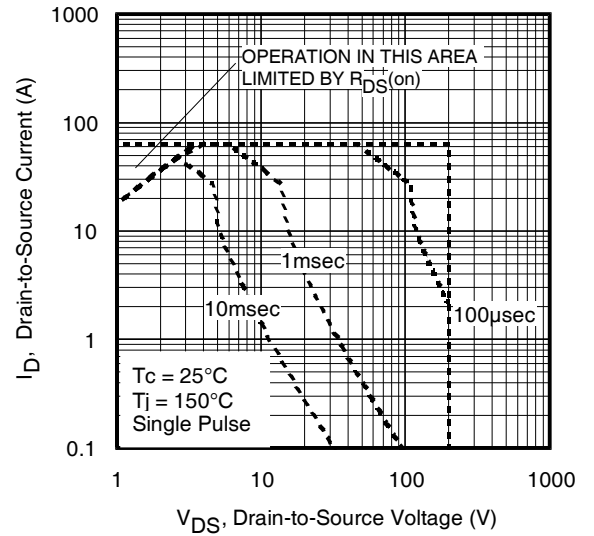


Fig 8. Maximum Safe Operating Area

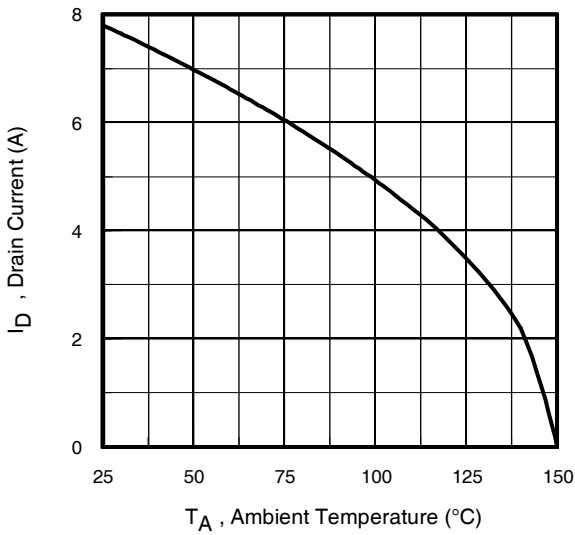


Fig 9. Maximum Drain Current Vs. Case (Top) Temperature

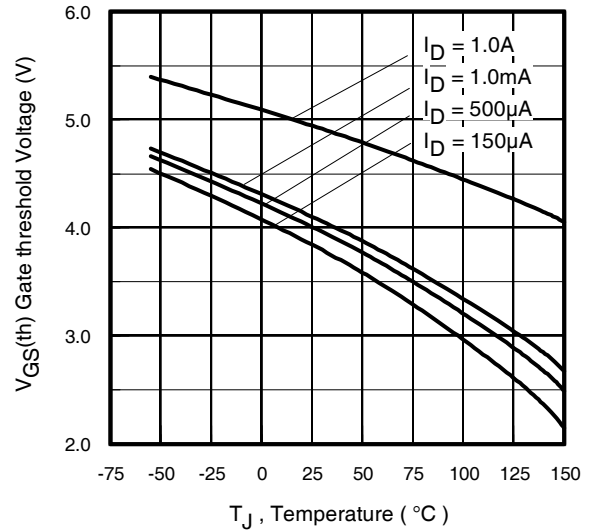


Fig 10. Threshold Voltage Vs. Temperature

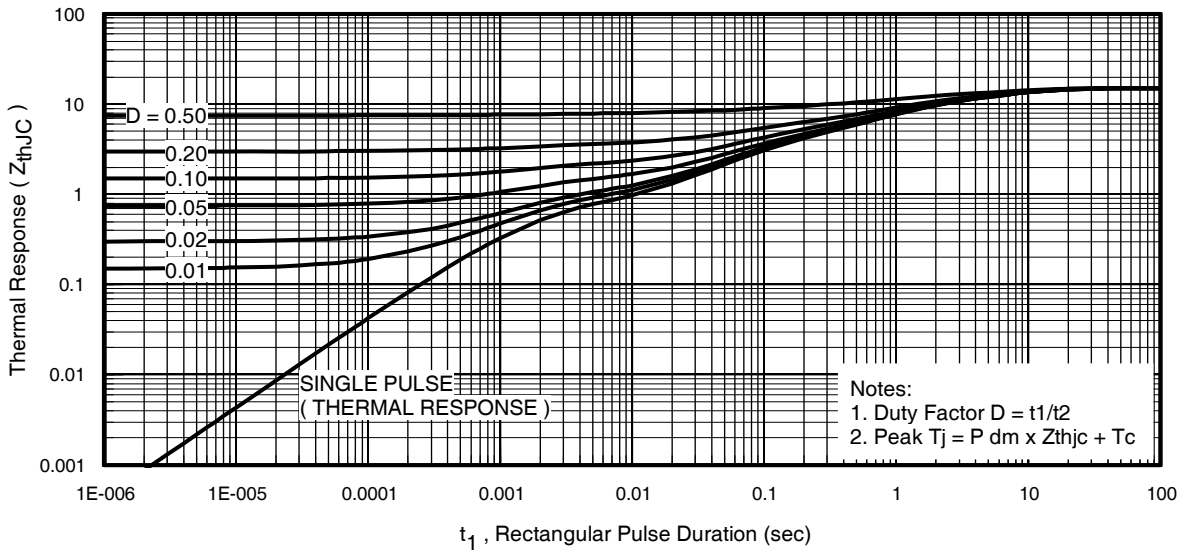


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Top)

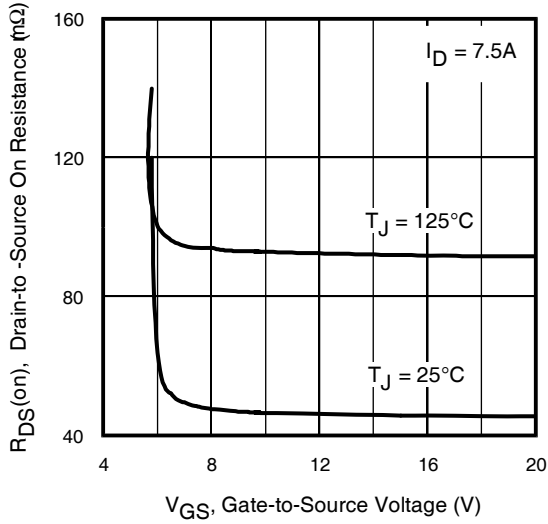


Fig 12. On-Resistance vs. Gate Voltage

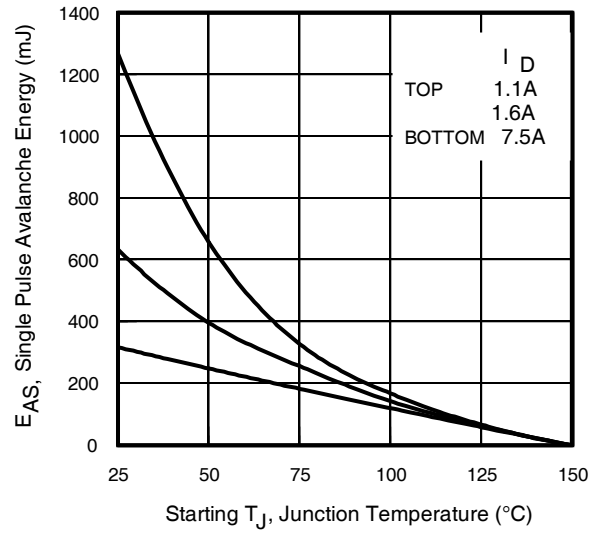


Fig 13. Maximum Avalanche Energy vs. Drain Current

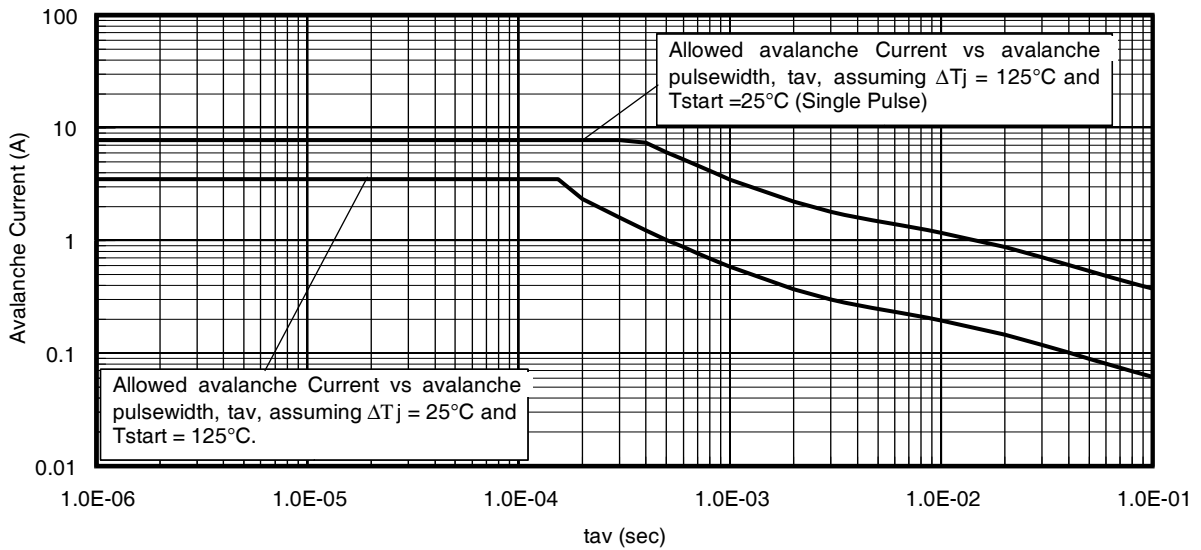
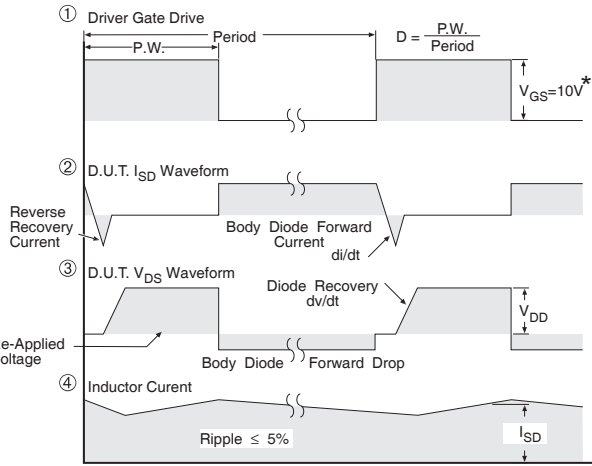
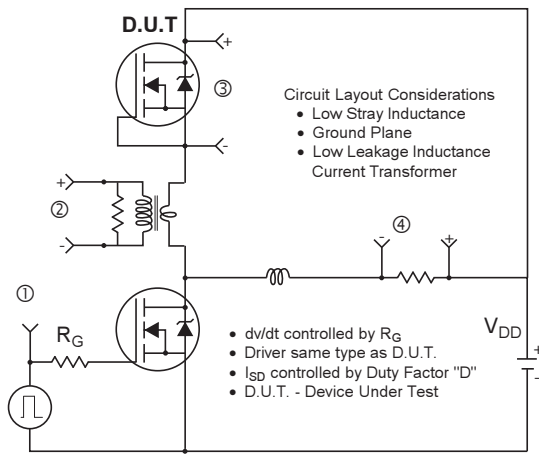


Fig 14. Typical Avalanche Current vs. Pulsewidth



* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

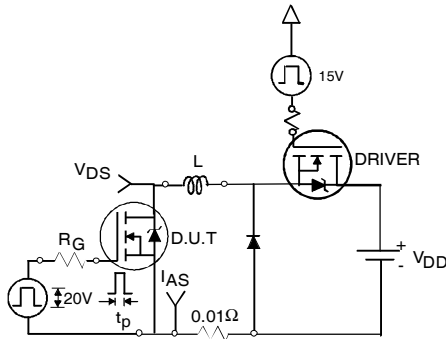


Fig 16a. Unclamped Inductive Test Circuit

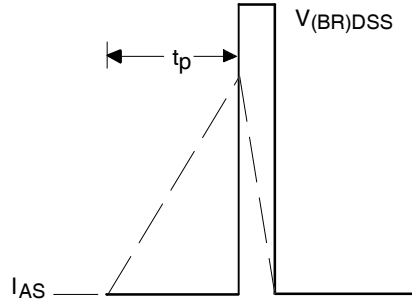


Fig 16b. Unclamped Inductive Waveforms

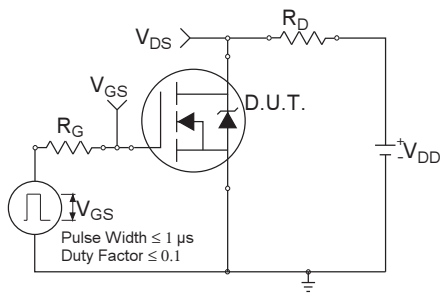


Fig 17a. Switching Time Test Circuit

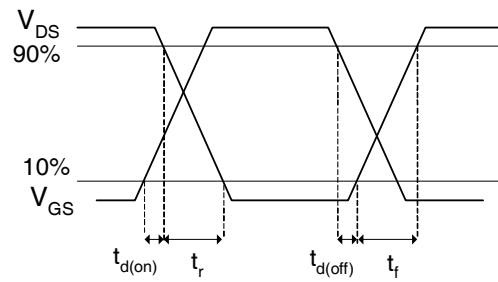


Fig 17b. Switching Time Waveforms

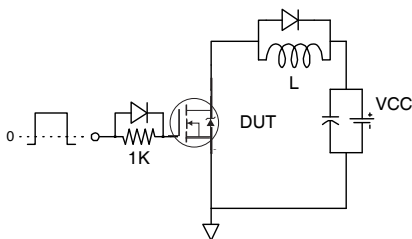


Fig 18a. Gate Charge Test Circuit

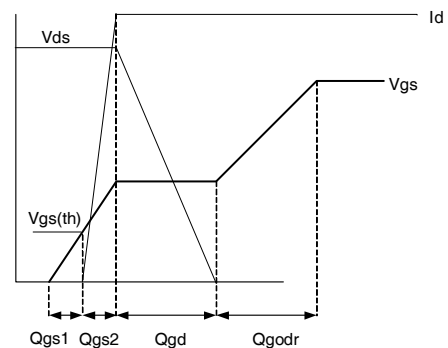
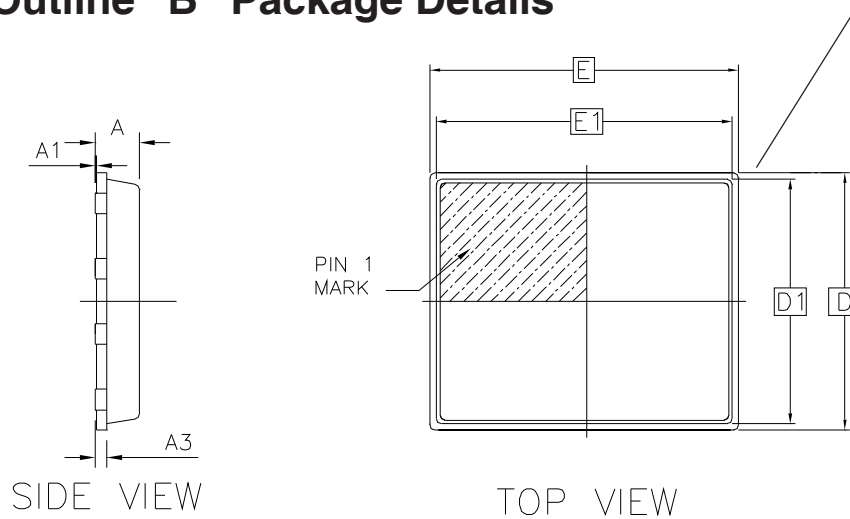
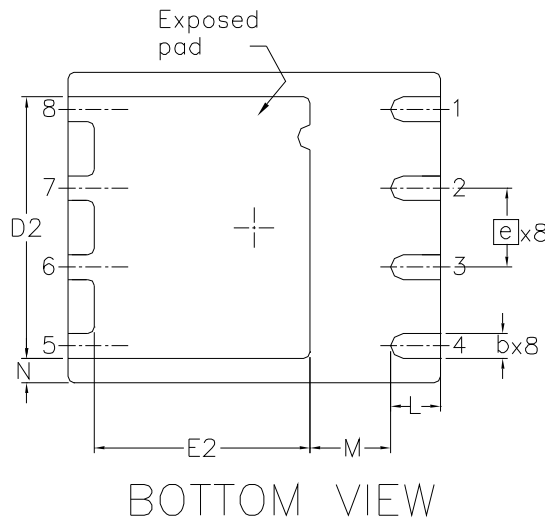


Fig 18b. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details

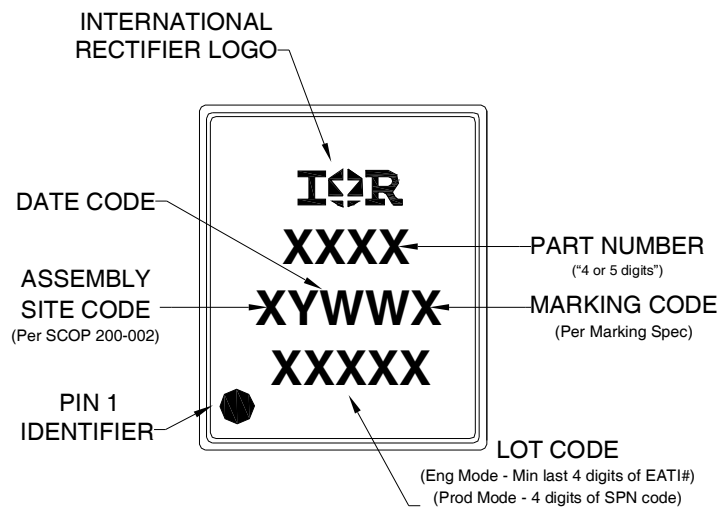


OUTLINE PQFN 5x6B			
DIM SYMBOL	MIN	NOM	MAX
A	0.80	0.83	0.90
A1	0	0.020	0.05
A3		0.20	REF
b	0.35	0.40	0.47
D		5.00	BSC
D1		4.75	BSC
D2	4.10	4.21	4.30
e		1.27	BSC
E		6.00	BSC
E1		5.75	BSC
E2	3.38	3.48	3.58
L	0.70	0.80	0.90
M		1.30	REF
N		0.40	REF



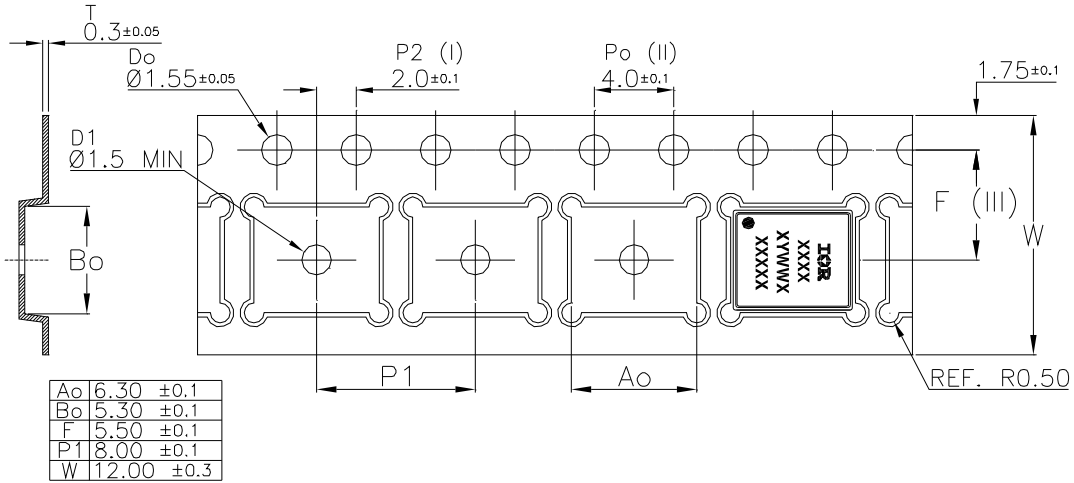
For footprint and stencil design recommendations, please refer to application note AN-1154 at <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>
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PQFN Tape and Reel



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industrial ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D ^{†††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 11.3\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 7.5\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 101N.Sepulveda blvd, El Segundo, California 90245, USA Tel: (310) 252-7105
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